

## AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

14. (Currently Amended) A method for integrating oxide removal from a semiconductor wafer and processing thereof, comprising:

- exposing a single semiconductor wafer in a transfer chamber module to a vaporous solution substantially inert with respect to the semiconductor wafer;
- removing ~~the~~ an oxide layer from the semiconductor wafer with the vaporous solution; and
- aligning the semiconductor wafer in the transfer chamber module for presentation to a process module.

15. (Currently Amended) The method of claim 14, further comprising:

- automatically transferring the semiconductor wafer into the process module from the a transfer chamber module; and
- intentionally adding at least one film layer to the semiconductor wafer in the process module.

16. (Original) The method of claim 14, wherein the vaporous solution comprises HF.

17. (Currently Amended) The method of claim 14, wherein the vaporous solution comprises .049% to 49% HF by volume.

18. (Original) The method of claim 14, wherein the oxide is a chemical oxide.

19. (Original) The method of claim 14, wherein the semiconductor wafer comprises silicon.

20. (Original) The method of claim 14, wherein the at least one film layer comprises one of the group consisting of  $\text{SiO}_2$ , epitaxial Si, polysilicon, and nitride.